MULTILAYER CERAMIC CHIP CAPACITORS

DESCRIPTION: CHIP SERIES (MA-Q TYPE)

The Pro-Cap Electronics MA-Q Series Ultra-Low ESR Capacitors are ideally suited for applications such as base station products, high Q Frequency sources, portable wireless systems, and RF integrated circuits. The unique combination of characteristics, performance, and high working voltage allows the MA-Q Series to exceed the dielectric RF performance of any other series capacitors and to meet or exceed EIA-198, MIL-PRF-55681 and MIL-PRF-123 requirements.

SELECTION OF CERAMIC CHIP CAPACITOR

1. DIELECTRIC TYPE

The choice of dielectric is determined by the required capacitance-temperature stability. We offer CG.

2. CAPACITANCE AND TOLERANCE

Capacitance and its tolerance are determined by circuit requirement and cost consideration.

3. RATED VOLTAGE

Rated voltage is determined by circuit requirement.

4. SIZE

Size is determined by the circuit design and cost consideration.

5. PACKAGING

Specify the packaging of Capacitors as TAPE & REEL.

6. NON-STANDARD REQUIREMENTS

Specify any non-standard requirements which are not stated in the catalogue.

Dielectric	CG
NPO	Ultra-Low ESR High Self Resonance Frequencies High Working Voltage Ultra Hi-Q NPO Dielectric

MA-Q Series - ULTRA-LOW ESR & HI-Q NPO



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MA-Q Series

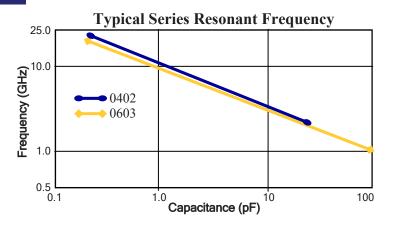


ENVIRONMENTAL CHARACTERISTICS

	Specification	Test Parameters
Solderability:	Solder coverage: 90% of metalized areas No termination degradation	Preheat chip to 120°C-150°C for 60 secs, dip terminals in rosin flux then dip in Sn62 solder @ 240°±5°C for ±1 sec
Resistance to Soldering Heat:	No mechanical damage. Capacitance change: ±2.5% or 0.25pF Q>500 I.R. >10G Ohms Breakdown Voltage: 2.5 x WVDC	Preheat device to 80°-100°C for 60 secs; followed by 150°-180°C for 60 secs.
Terminal Adhesion:	Termination should not pull off. Ceramic should remain undamaged.	Linear pull force exerted on axial leads soldered to each terminal. (2lbs for 0402; 2lbs for 0603)
PCB Deflection:	No mechanical damage. Capacitance change: 2% or 0.5pF Max	Glass epoxy PCB; 0.5 mm deflection.
Life Test:	No mechanical damage. Capacitance change: ±3.0% or 0.3pF Q>500 I.R. >1G Ohms Breakdown Voltage: 2.5 x WVDC	Applied voltage: 200% rated voltage, 50mA max. Temperature: 125°±3°C Test time: 1000 +48 hours, -0 hours.
Thermal Cycle:	No mechanical damage. Capacitance change: ±2.5% or 0.25pF Q>2000 I.R. >10G Ohms Breakdown Voltage: 2.5 x WVDC	5 cycles of: 30±3 min. @ -55°+0/-3°C, 2-3 min. @ 25°C, 30±3 min. @ +125°C=3/-0°C, 2-3 mins. @ 25°C Measure after 24±2 hour cooling period.
Humidity, Steady State:	No mechanical damage. Capacitance change: ±5.0% or 0.5pF max. Q>300 I.R. = 1G Ohms Breakdown Voltage: 2.5 x WVDC	Relative humidity: 90-95% Temperature: 40°±2°C Test time: 500 + 12/-0 hours. Measure time after 24±2 hour cooling period.
Humidity, Low Voltage:	No mechanical damage. Capacitance change: ±5.0% or 0.5pF max. Q>300 I.R. = 1G Ohms min. Breakdown Voltage: 2.5 x WVDC	Applied voltage: 1.5 VDC, 50 mA max Relative humidity: 85±2%; Temperature: 40°±2°C Test time: 240 + 12/-0 hours. Measure after 24±2 hour cooling period.
Vibration:	No mechanical damage. Capacitance change: ±2.5% or 0.25pF max. Q>1000 I.R. = 10G Ohms Breakdown Voltage: 2.5 x WVDC	Cycle performed for 2 hours in each of three perpendicular directions. Frequency range 10Hz to 55 Hz to 10 Hz traversed in 1 min Harmonic motion amplitude: 1.5mm.

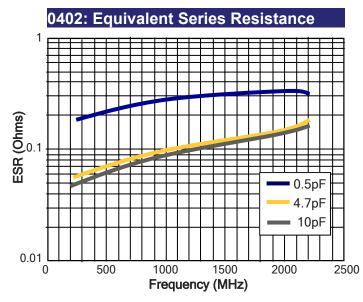
DIELECTRIC CHARACTERISTICS

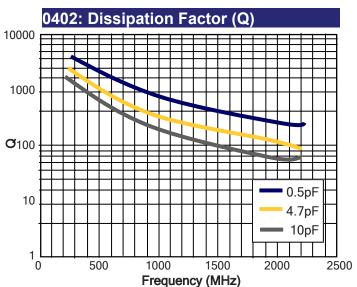
Temperature Coefficient	0 ± 30ppm / °C, -55 to 125°C	
Quality Factor:		
Insulation Resistance:	> 10G @ 25°C, WVDC; 125°C IR is 10% of 25 rating	
Dielectric Strength:	2.5 x WVDC min, 25°C, 50 mA max	
Test Parameters:	1MHz ± 50kHz 1.0 ± 0.2, VRMS, 25°C	
Available Capacitance:	0201 Size: 0.2 - 20pF 0402 Size: 0.2 - 33pF 0603 Size: 0.2 - 100pF 0805 Size: 0.3 - 220pF	

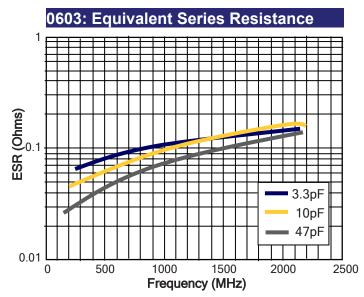


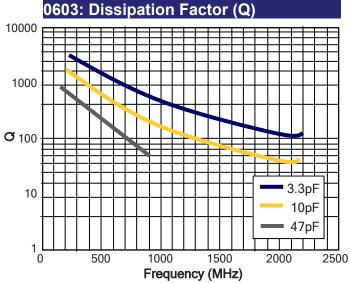
MULTILAYER CERAMIC CHIP CAPACITORS

RF CHARACTERISTICS VERSUS FREQUENCY











- ULTRA-LOW ESR & HI-Q NPO

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- ULTRA-LOW ESR & HI-Q NPO

RF CHARACTERISTICS VERSUS CAPACITANCE

